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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, Motor Control PWM, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	112
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 21x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LFBGA
Supplier Device Package	144-LFBGA (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f103zdh6tr

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2.3.14 Low-power modes

The STM32F103xC, STM32F103xD and STM32F103xE performance line supports three low-power modes to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- **Sleep mode**
In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.
- **Stop mode**
Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.
The device can be woken up from Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm or the USB wakeup.
- **Standby mode**
The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.8 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the Backup domain and Standby circuitry.
The device exits Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped by entering Stop or Standby mode.

2.3.15 DMA

The flexible 12-channel general-purpose DMAs (7 channels for DMA1 and 5 channels for DMA2) are able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The two DMA controllers support circular buffer management, removing the need for user code intervention when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with support for software trigger on each channel. Configuration is made by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I²C, USART, general-purpose, basic and advanced-control timers TIMx, DAC, I²S, SDIO and ADC.

2.3.16 RTC (real-time clock) and backup registers

The RTC and the backup registers are supplied through a switch that takes power either on V_{DD} supply when present or through the V_{BAT} pin. The backup registers are forty-two 16-bit registers used to store 84 bytes of user application data when V_{DD} power is not present. They are not reset by a system or power reset, and they are not reset when the device wakes up from the Standby mode.

The real-time clock provides a set of continuously running counters which can be used with suitable software to provide a clock calendar function, and provides an alarm interrupt and a

the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

2.3.18 I²C bus

Up to two I²C bus interfaces can operate in multimaster and slave modes. They can support standard and fast modes.

They support 7/10-bit addressing mode and 7-bit dual addressing mode (as slave). A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SMBus 2.0/PMBus.

2.3.19 Universal synchronous/asynchronous receiver transmitters (USARTs)

The STM32F103xC, STM32F103xD and STM32F103xE performance line embeds three universal synchronous/asynchronous receiver transmitters (USART1, USART2 and USART3) and two universal asynchronous receiver transmitters (UART4 and UART5).

These five interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability.

The USART1 interface is able to communicate at speeds of up to 4.5 Mbit/s. The other available interfaces communicate at up to 2.25 Mbit/s.

USART1, USART2 and USART3 also provide hardware management of the CTS and RTS signals, Smart Card mode (ISO 7816 compliant) and SPI-like communication capability. All interfaces can be served by the DMA controller except for UART5.

2.3.20 Serial peripheral interface (SPI)

Up to three SPIs are able to communicate up to 18 Mbits/s in slave and master modes in full-duplex and simplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

All SPIs can be served by the DMA controller.

2.3.21 Inter-integrated sound (I²S)

Two standard I²S interfaces (multiplexed with SPI2 and SPI3) are available, that can be operated in master or slave mode. These interfaces can be configured to operate with 16/32 bit resolution, as input or output channels. Audio sampling frequencies from 8 kHz up to 48 kHz are supported. When either or both of the I²S interfaces is/are configured in master

5.3.4 Embedded reference voltage

The parameters given in [Table 13](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 10](#).

Table 13. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	$-40\text{ }^{\circ}\text{C} < T_A < +105\text{ }^{\circ}\text{C}$	1.16	1.20	1.26	V
		$-40\text{ }^{\circ}\text{C} < T_A < +85\text{ }^{\circ}\text{C}$	1.16	1.20	1.24	
$T_{S_vrefint}^{(1)}$	ADC sampling time when reading the internal reference voltage	-	-	5.1	17.1 ⁽²⁾	μs
$V_{RERINT}^{(2)}$	Internal reference voltage spread over the temperature range	$V_{DD} = 3\text{ V} \pm 10\text{ mV}$	-	-	10	mV
$T_{Ccoeff}^{(2)}$	Temperature coefficient	-	-	-	100	ppm/ $^{\circ}\text{C}$

1. Shortest sampling time can be determined in the application by multiple iterations.

2. Guaranteed by design.

5.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in [Figure 13: Current consumption measurement scheme](#).

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code.

Maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f_{HCLK} frequency (0 wait state from 0 to 24 MHz, 1 wait state from 24 to 48 MHz and 2 wait states above)
- Prefetch in ON (reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled $f_{PCLK1} = f_{HCLK}/2$, $f_{PCLK2} = f_{HCLK}$

The parameters given in [Table 14](#), [Table 15](#) and [Table 16](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 10](#).

Table 14. Maximum current consumption in Run mode, code with data processing running from Flash

Symbol	Parameter	Conditions	f _{HCLK}	Max ⁽¹⁾		Unit
				T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in Run mode	External clock ⁽²⁾ , all peripherals enabled	72 MHz	69	70	mA
			48 MHz	50	50.5	
			36 MHz	39	39.5	
			24 MHz	27	28	
			16 MHz	20	20.5	
			8 MHz	11	11.5	
		External clock ⁽²⁾ , all peripherals disabled	72 MHz	37	37.5	
			48 MHz	28	28.5	
			36 MHz	22	22.5	
			24 MHz	16.5	17	
			16 MHz	12.5	13	
			8 MHz	8	8	

1. Guaranteed by characterization results.

2. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

Table 15. Maximum current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditions	f _{HCLK}	Max ⁽¹⁾		Unit
				T _A = 85 °C	T _A = 105 °C	
I _{DD}	Supply current in Run mode	External clock ⁽²⁾ , all peripherals enabled	72 MHz	66	67	mA
			48 MHz	43.5	45.5	
			36 MHz	33	35	
			24 MHz	23	24.5	
			16 MHz	16	18	
			8 MHz	9	10.5	
		External clock ⁽²⁾ , all peripherals disabled	72 MHz	33	33.5	
			48 MHz	23	23.5	
			36 MHz	18	18.5	
			24 MHz	13	13.5	
			16 MHz	10	10.5	
			8 MHz	6	6.5	

1. Guaranteed by characterization results at V_{DD} max, f_{HCLK} max.

2. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

Figure 14. Typical current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals enabled

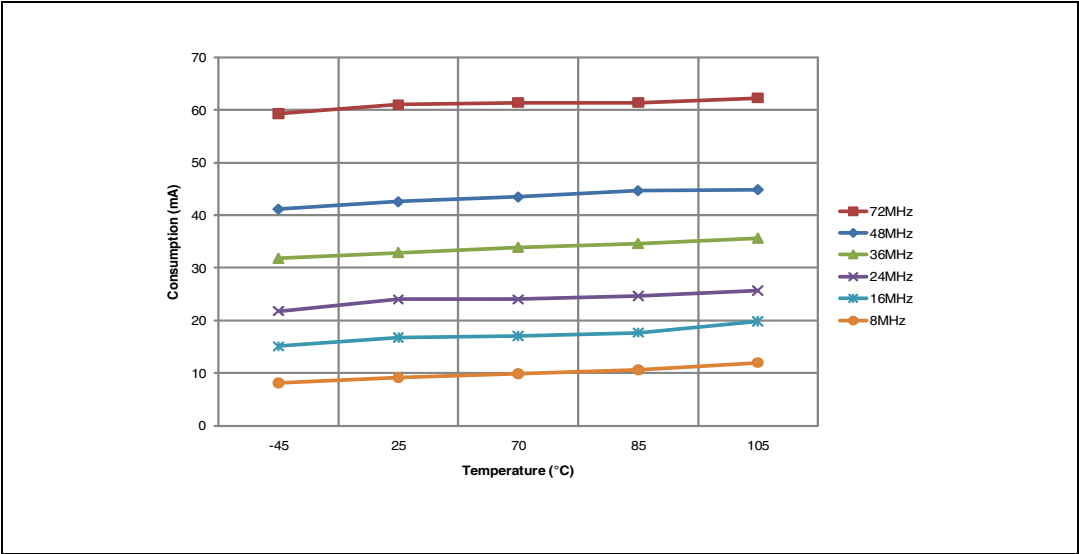


Figure 15. Typical current consumption in Run mode versus frequency (at 3.6 V)- code with data processing running from RAM, peripherals disabled

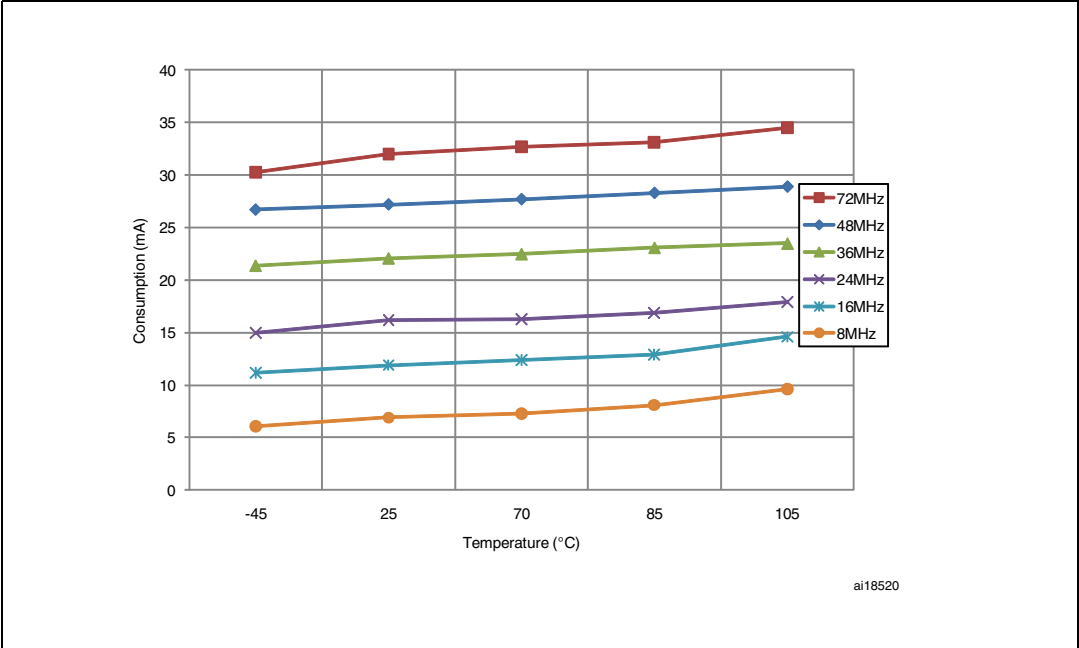


Table 20. Peripheral current consumption (continued)

Peripheral		Current consumption	Unit
APB2 (up to 72 MHz)	APB2-Bridge	4,17	$\mu\text{A}/\text{MHz}$
	GPIOA	8,47	
	GPIOB	8,47	
	GPIOC	6,53	
	GIOD	8,47	
	GPIOE	6,53	
	GPIOF	6,53	
	GPIOG	6,11	
	SPI1	4,72	
	USART1	12,50	
	TIM1	22,92	
	TIM8	22,92	
	ADC1 ⁽⁴⁾	17,32	
	ADC2 ⁽⁴⁾	15,18	
	ADC3 ⁽⁴⁾	14,82	

1. The BusMatrix is automatically active when at least one master is ON. (CPU, DMA1 or DMA2).
2. When the I2S is enabled, a current consumption equal to 0.02 mA must be added.
3. When DAC_OUT1 or DAC_OUT2 is enabled, a current consumption equal to 0.36 mA must be added.
4. Specific conditions for measuring ADC current consumption: $f_{\text{HCLK}} = 56 \text{ MHz}$, $f_{\text{APB1}} = f_{\text{HCLK}}/2$, $f_{\text{APB2}} = f_{\text{HCLK}}$, $f_{\text{ADCCLK}} = f_{\text{APB2}}/4$. When ADON bit in the ADCx_CR2 register is set to 1, a current consumption of analog part equal to 0.54 mA must be added for each ADC.

Table 30. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min ⁽¹⁾	
N _{END}	Endurance	T _A = -40 to +85 °C (6 suffix versions) T _A = -40 to +105 °C (7 suffix versions)	10	kcycles
t _{RET}	Data retention	1 kcycle ⁽²⁾ at T _A = 85 °C	30	Years
		1 kcycle ⁽²⁾ at T _A = 105 °C	10	
		10 kcycles ⁽²⁾ at T _A = 55 °C	20	

1. Guaranteed by characterization results.

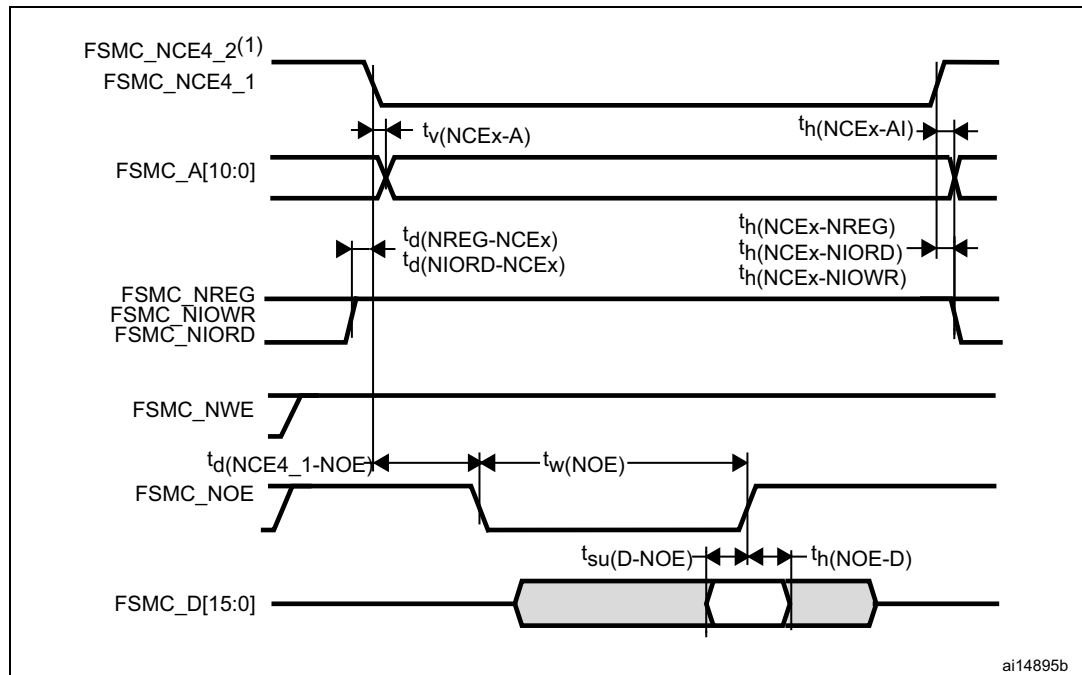
2. Cycling performed over the whole temperature range.

PC Card/CompactFlash controller waveforms and timings

Figure 32 through Figure 37 represent synchronous waveforms and Table 39 provides the corresponding timings. The results shown in this table are obtained with the following FSMC configuration:

- COM.FSMC_SetupTime = 0x04;
- COM.FSMC_WaitSetupTime = 0x07;
- COM.FSMC_HoldSetupTime = 0x04;
- COM.FSMC_HiZSetupTime = 0x00;
- ATT.FSMC_SetupTime = 0x04;
- ATT.FSMC_WaitSetupTime = 0x07;
- ATT.FSMC_HoldSetupTime = 0x04;
- ATT.FSMC_HiZSetupTime = 0x00;
- IO.FSMC_SetupTime = 0x04;
- IO.FSMC_WaitSetupTime = 0x07;
- IO.FSMC_HoldSetupTime = 0x04;
- IO.FSMC_HiZSetupTime = 0x00;
- TCLRSetupTime = 0;
- TARSetupTime = 0;

Figure 32. PC Card/CompactFlash controller waveforms for common memory read access



1. FSMC_NCE4_2 remains high (inactive during 8-bit access).

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 42. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f _{HSE} /f _{HCLK}]		Unit
				8/48 MHz	8/72 MHz	
S _{EMI}	Peak level	V _{DD} = 3.3 V, T _A = 25 °C, LQFP144 package compliant with IEC 61967-2	0.1 to 30 MHz	8	12	dBμV
			30 to 130 MHz	31	21	
			130 MHz to 1GHz	28	33	
			SAE EMI Level	4	4	-

5.3.12 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 43. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C, conforming to JESD22-A114	2	2000	V
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C, conforming to JESD22-C101	III	500	

1. Guaranteed by characterization results.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Figure 42. Standard I/O input characteristics - CMOS port

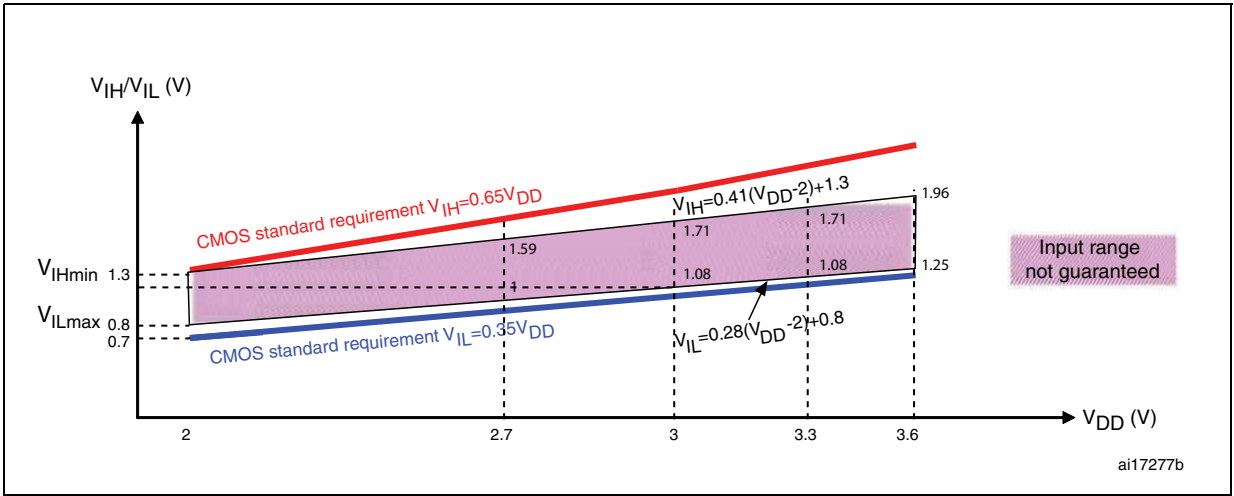


Figure 43. Standard I/O input characteristics - TTL port

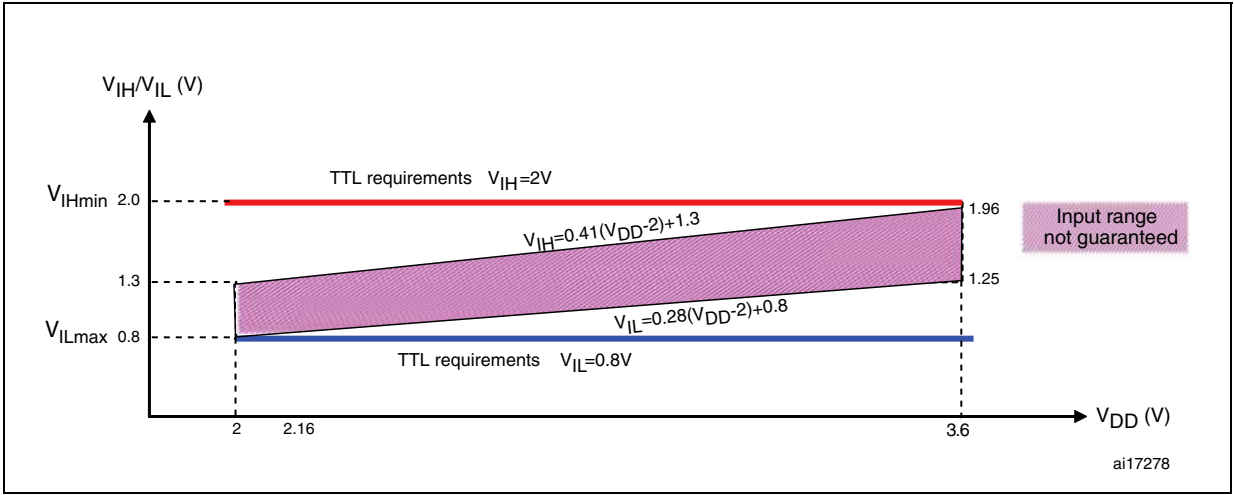


Figure 44. 5 V tolerant I/O input characteristics - CMOS port

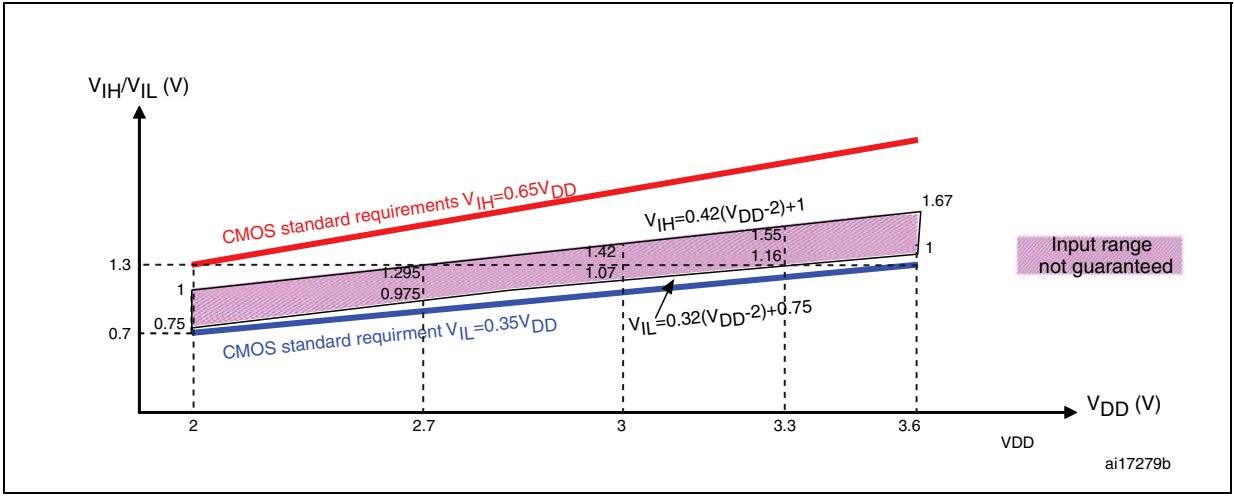
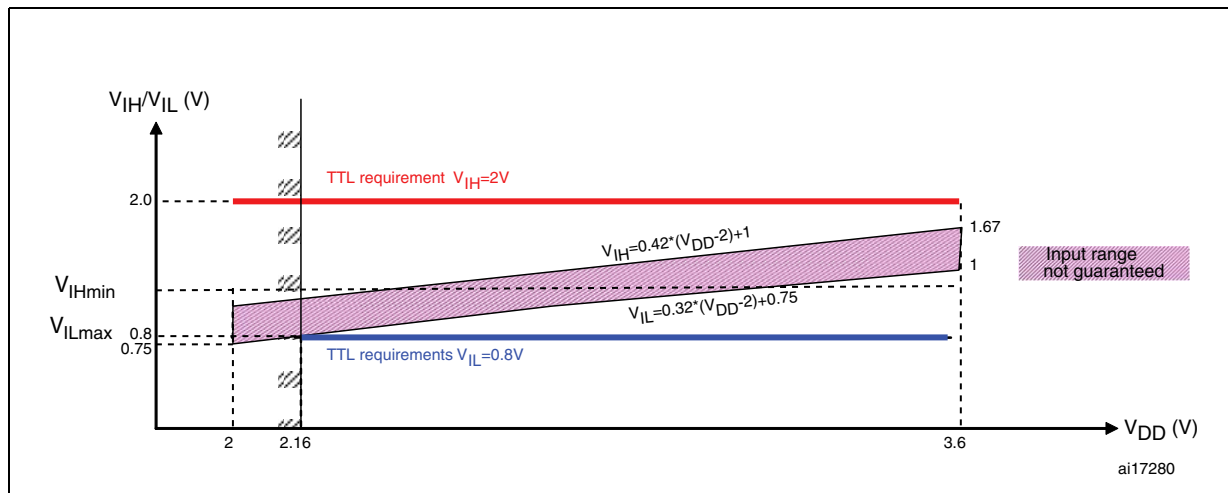


Figure 45. 5 V tolerant I/O input characteristics - TTL port



Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 20 mA (with a relaxed V_{OL}/V_{OH}) except PC13, PC14 and PC15 which can sink or source up to ± 3 mA. When using the GPIOs PC13 to PC15 in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 5.2](#):

- The sum of the currents sourced by all the I/Os on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating I_{VDD} (see [Table 8](#)).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating I_{VSS} (see [Table 8](#)).

Output voltage levels

Unless otherwise specified, the parameters given in [Table 47](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 10](#). All I/Os are CMOS and TTL compliant.

Table 47. Output voltage characteristics

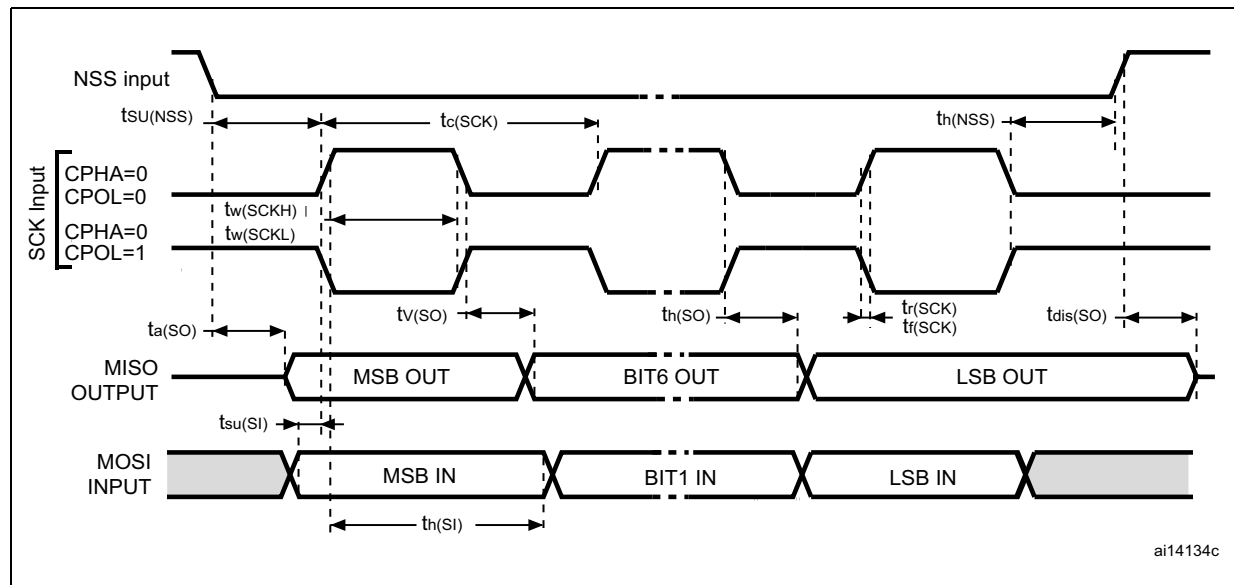
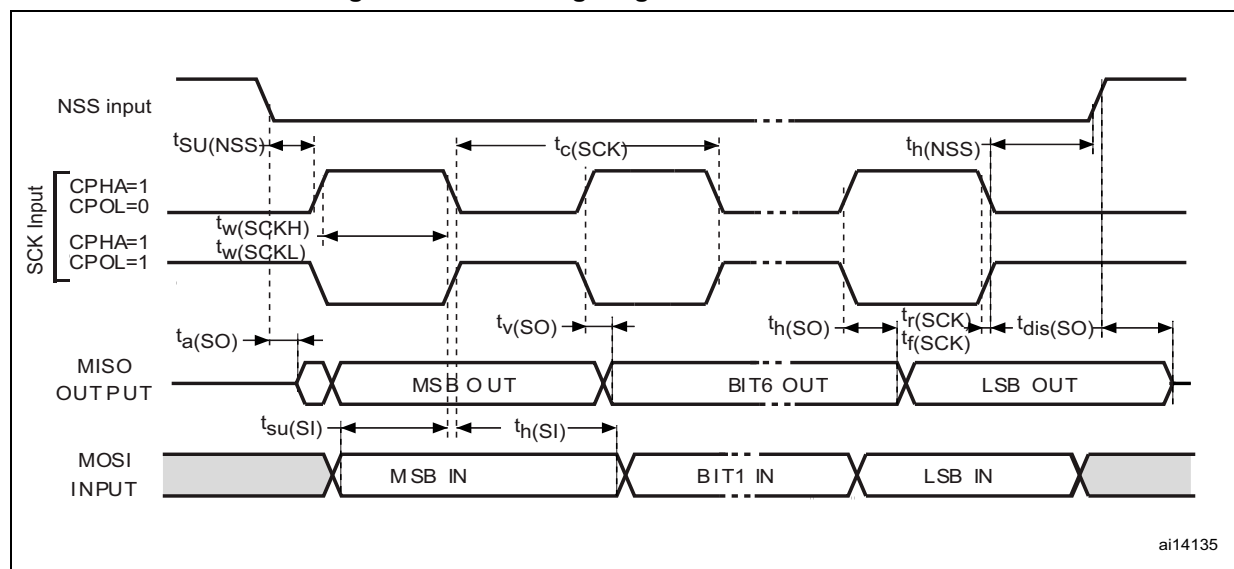
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin when 8 pins are sunk at same time	TTL port ⁽³⁾ $I_{IO} = +8$ mA $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	0.4	V
$V_{OH}^{(2)}$	Output high level voltage for an I/O pin when 8 pins are sourced at same time		$V_{DD}-0.4$	-	
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin when 8 pins are sunk at same time	CMOS port ⁽³⁾ $I_{IO} = +8$ mA $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	0.4	V
$V_{OH}^{(2)}$	Output high level voltage for an I/O pin when 8 pins are sourced at same time		2.4	-	

Table 47. Output voltage characteristics (continued)

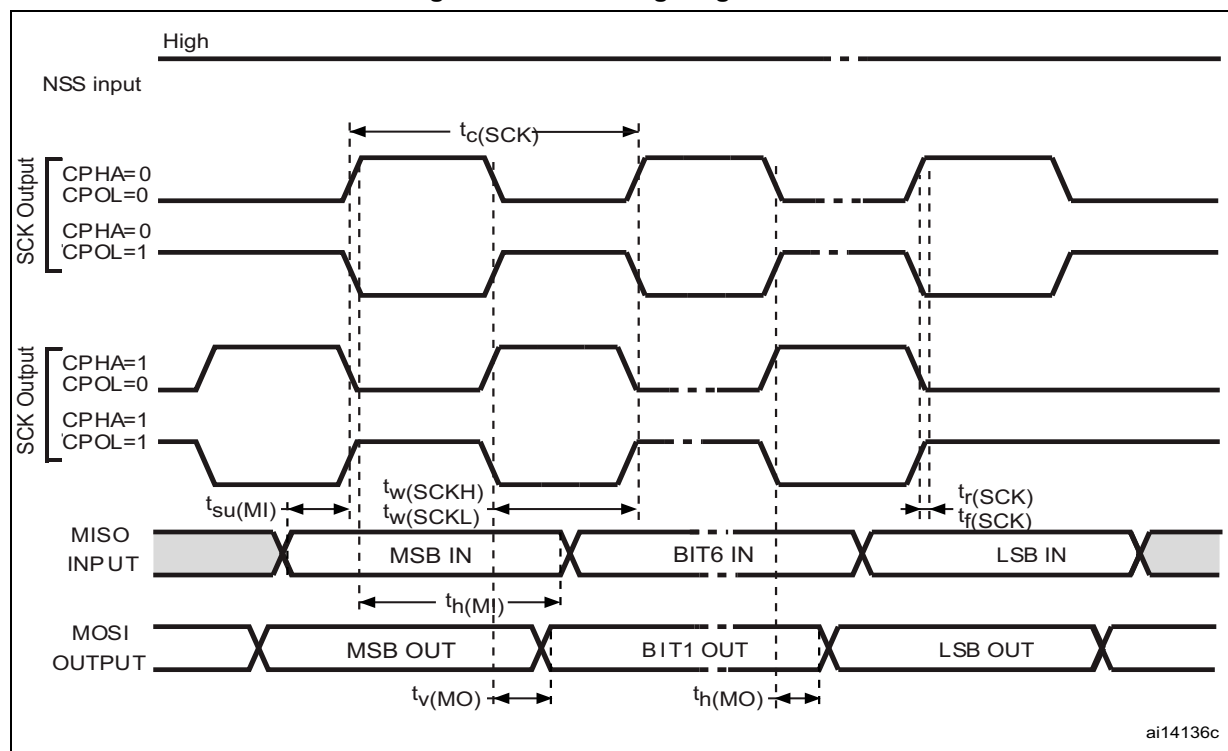
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin when 8 pins are sunk at same time	$I_{IO} = +20\text{ mA}$ $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	1.3	V
$V_{OH}^{(2)(4)}$	Output high level voltage for an I/O pin when 8 pins are sourced at same time		$V_{DD}-1.3$	-	
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin when 8 pins are sunk at same time	$I_{IO} = +6\text{ mA}$ $2\text{ V} < V_{DD} < 2.7\text{ V}$	-	0.4	V
$V_{OH}^{(2)(4)}$	Output high level voltage for an I/O pin when 8 pins are sourced at same time		$V_{DD}-0.4$	-	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in [Table 8](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS} .
2. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in [Table 8](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD} .
3. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
4. Guaranteed by characterization results.

Figure 49. SPI timing diagram - slave mode and CPHA = 0

Figure 50. SPI timing diagram - slave mode and CPHA = 1⁽¹⁾

1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Figure 51. SPI timing diagram - master mode⁽¹⁾

1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

SD/SDIO MMC card host interface (SDIO) characteristics

Unless otherwise specified, the parameters given in [Table 55](#) are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 10](#).

Refer to [Section 5.3.14: I/O port characteristics](#) for more details on the input/output alternate function characteristics (D[7:0], CMD, CK).

Figure 54. SDIO high-speed mode

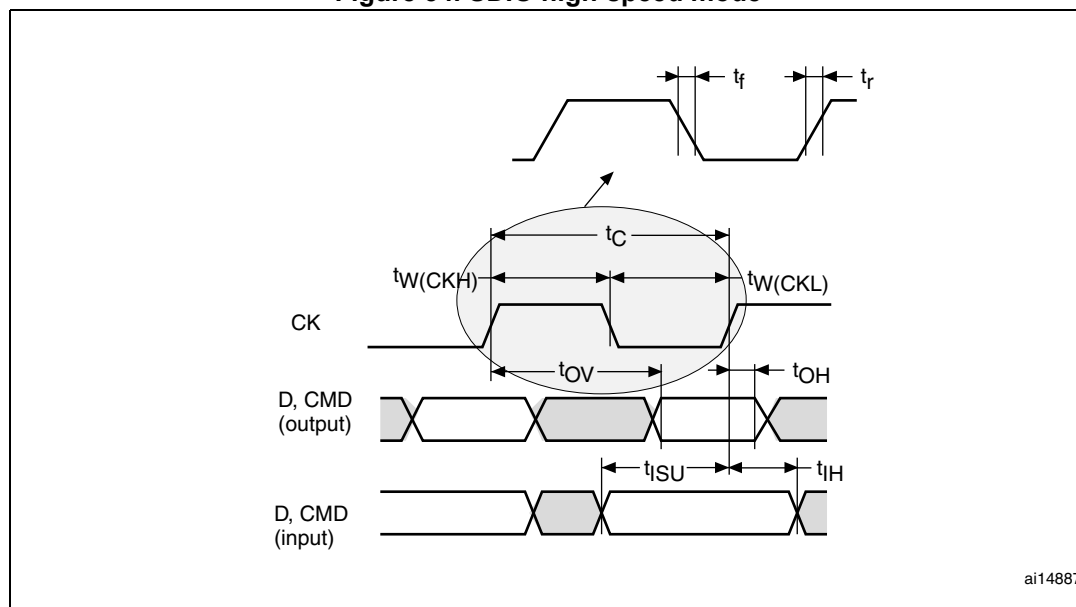


Figure 55. SD default mode

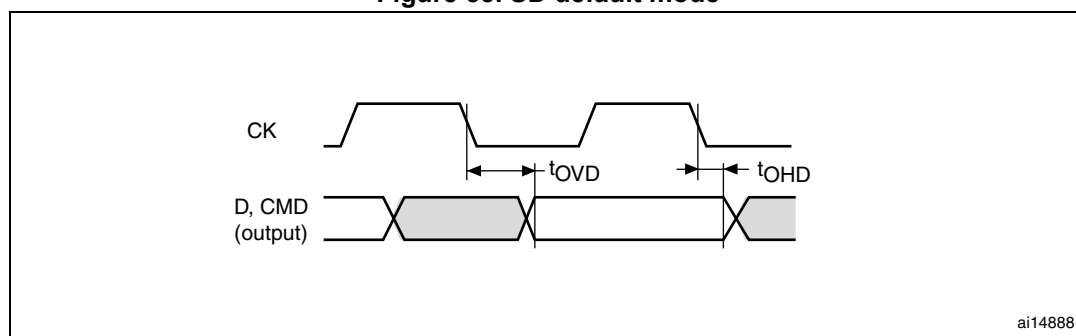
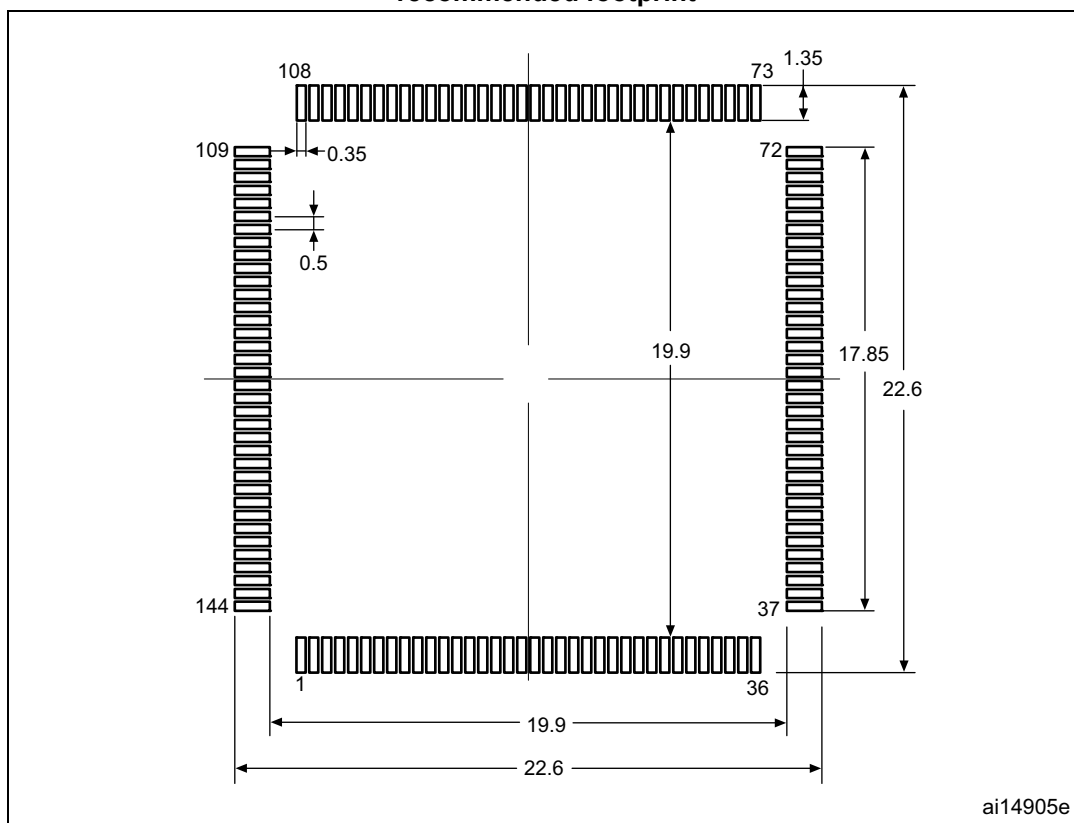


Table 55. SD / MMC characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{PP}	Clock frequency in data transfer mode	$C_L \leq 30$ pF	0	48	MHz
$t_W(CKL)$	Clock low time, $f_{PP} = 16$ MHz	$C_L \leq 30$ pF	32	-	ns
$t_W(CKH)$	Clock high time, $f_{PP} = 16$ MHz	$C_L \leq 30$ pF	30	-	
t_r	Clock rise time	$C_L \leq 30$ pF	-	4	
t_f	Clock fall time	$C_L \leq 30$ pF	-	5	

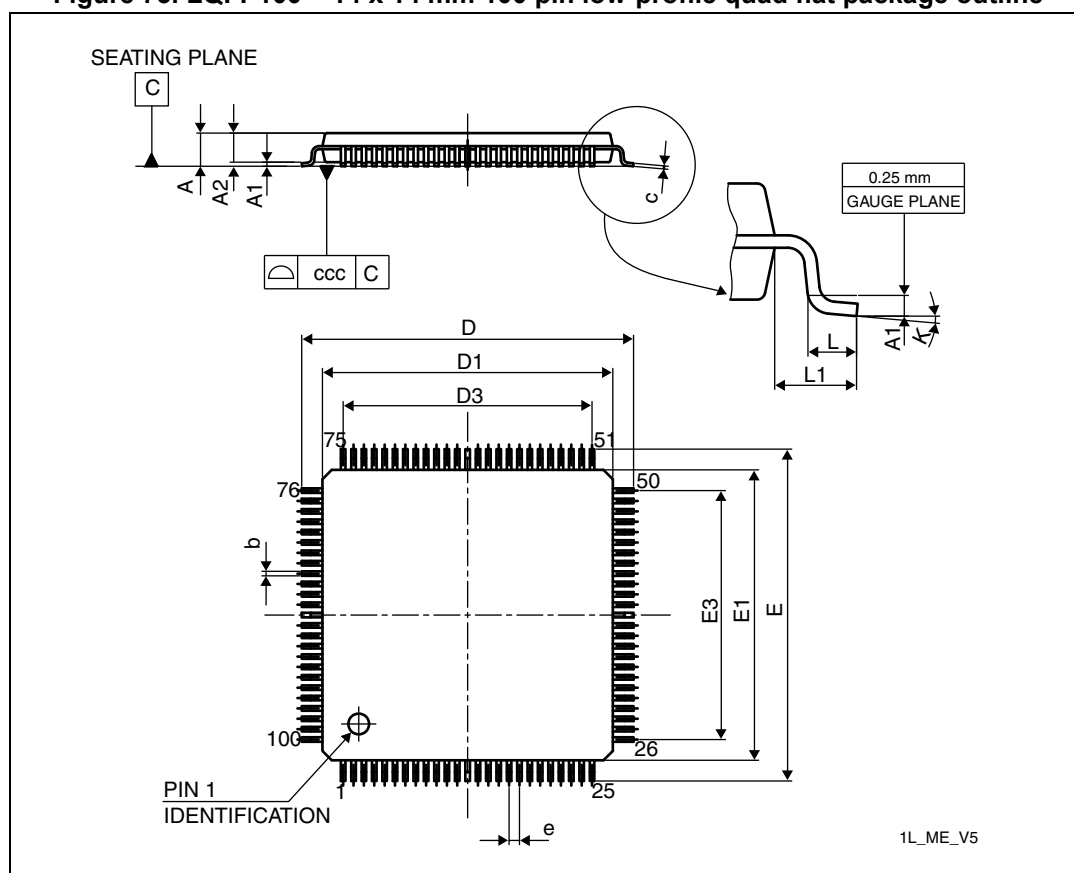
Figure 71. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

6.5 LQFP100 package information

Figure 73. LQFP100 – 14 x 14 mm 100 pin low-profile quad flat package outline



1. Drawing is not to scale.

Table 72. LQFP100 – 14 x 14 mm 100-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-

Table 76.Document revision history

Date	Revision	Changes
31-08-2015	11	<p>Replaced USBDP and USBDM by USB_DP and USB_DM in the whole document.</p> <p>Updated:</p> <ul style="list-style-type: none"> – Introduction – Reference standard in Table 43: ESD absolute maximum ratings. – Updated I_{DDA} description in Table 63: DAC characteristics. – Section : I2C interface characteristics – Figure 62: LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package outline – Updated sentence before Figure 78: LQFP64 marking example (package top view). – Figure 65: LFBGA100 - 10 x 10 mm low profile fine pitch ball grid array package outline and sentence before Figure 75: LQFP100 marking example (package top view) – Figure 68: WLCSP, 64-ball 4.466 × 4.395 mm, 0.500 mm pitch, wafer-level chip-scale package outline – Figure 48: I2C bus AC waveforms and measurement circuit on page 98 – Section 6.1: LFBGA144 package information and Section 6.2: LFBGA100 package information. – Table 20: Peripheral current consumption <p>Added:</p> <ul style="list-style-type: none"> – Figure 63: LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package recommended footprint – Figure 64: LFBGA144 marking example (package top view) – Figure 66: LFBGA100 – 100-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package recommended footprintoutline – Figure 69: WLCSP64 - 64-ball, 4.4757 x 4.4049 mm, 0.5 mm pitch wafer level chip scale package recommended footprint – Table 66: LFBGA144 recommended PCB design rules (0.8 mm pitch BGA) – Table 68: LFBGA100 recommended PCB design rules (0.8 mm pitch BGA) – Table 70: WLCSP64 recommended PCB design rules (0.5 mm pitch).
26-Nov-2015	12	<p>Updated:</p> <ul style="list-style-type: none"> – Table 59: ADC characteristics – Table 65: LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package mechanical data – Table 66: LFBGA144 recommended PCB design rules (0.8 mm pitch BGA) <p>Added:</p> <ul style="list-style-type: none"> – Note 3 on Table 7: Voltage characteristics